
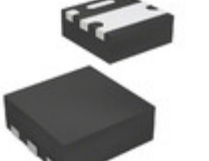
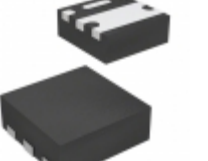


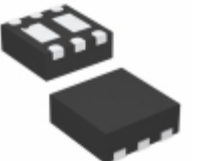
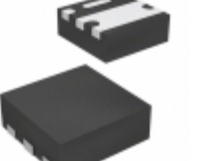
	<h2>SIA483DJ-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIA483DJ-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 30V 12A SC70-6</p> <p>Datenblätter:  SIA483DJ-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 22052 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIA483DJ-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 30V 12A SC70-6
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	22052 pcs Stock
Hersteller Standard Vorlaufzeit	32 Weeks
detaillierte Beschreibung	P-Channel 30V 12A (Tc) 3.5W (Ta), 19W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SC-70-6
Supplier Device-Gehäuse	PowerPAK® SC-70-6 Single
Verlustleistung (max)	3.5W (Ta), 19W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	12A (Tc)
Rds On (Max) @ Id, Vgs	21 mOhm @ 5A, 10V
VGS (th) (Max) @ Id	2.2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	45nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1550pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIA483DJ-T1-GE3TR

SIA483DJ-T1-GE3 ist neu im Original, Suche SIA483DJ-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIA483DJ-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIA483DJ-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIA477EDJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 12A SC-70-6L</p>	 <p>SIA511DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N/P-CH 12V 4.5A SC70-6</p>	 <p>SIA477EDJ-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V 12A SC-70-6L</p>	 <p>SIA513DJ-T1-E3 VISHAY SIA513DJ-T1-E3 VISHAY</p>
 <p>SIA485DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CHANNEL 150V 1.6A</p>	 <p>SIA511DJ-T1-GE3 Vishay / Siliconix MOSFET N/P-CH 12V 4.5A SC70-6</p>	 <p>SIA477EDJT-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V 12A SC70-6</p>	 <p>SIA513DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N/P-CH 20V 4.5A SC70-6</p>

heiße Teile

Mehr

⊛ SIA433EDJ	↔ SIA433EDJ-T1-GE3	⇒ SIA433EDJ-T1-GE3	D SIA436DJ-T1-GE3	↔ SIA436DJ-T1-GE3
⊠ SIA443DJ-T1-GE3	⊛ SIA443DJ-T1-GE3	D SIA444DJ-T1-GE3	⇒ SIA444DJ-T1-GE3	↔ SIA445EDJ-T1-GE3
⊛ SIA445EDJ-T1-GE3	⊠ SIA447DJ-T1-GE3	⊛ SIA447DJ-T1-GE3	↔ SIA448DJ-T1-GE3	↔ SIA448DJ-T1-GE3
D SIA449DJ-GE3	⊛ SIA450DJ-T1-GE3	⊠ SIA450DJ-T1-GE3	⊛ SIA4528-100K	↔ SIA4528-330K
⇒ SIA4528-470K	↔ SIA453EDJ-T1-GE3	⊛ SIA453EDJ-T1-GE3	⊠ SIA456DJ-T1-GE3	↔ SIA456DJ-T1-GE3
↔ SIA483DJ-T1-GE3	⇒ SIA513DJ-T1-E3	D SIA517DJ-T1-GE3	⊛ SIA517DJ-T1-GE3	⊠ SIA517DJ-T4-GE3
⊛ SIA519EDJ-T1-GE3	D SIA519EDJ-T1-GE3	⇒ SIA533EDJ-T1-GE3	↔ SIA533EDJ-T1-GE3	↔ SIA778DJ-T1-GE3
⊠ SIA778DJ-T1-GE3	⊛ SIA811ADJ-T1-GE3	↔ SIA811ADJ-T1-GE3	⇒ SIA811DJ-T1	↔ SIA811DJ-T1-E3
⊛ SIA811DJ-T1-E3	⊠ SIA811DJ-T1-GE3	⊛ SIA811DJ-T1-GE3	D SIA813DJ-T1-GE3	↔ SIA813DJ-T1-GE3
↔ SIA814DJ-T1-GE3	⊛ SIA814DJ-T1-GE3	⊠ SIA906EDJ-T1-GE3	⊛ SIA906EDJ-T1-GE3	↔ SIA906EDJ-T4-GE3

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